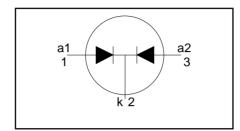
## PBYR245CT series

### **FEATURES**

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- low profile surface mounting package

### **SYMBOL**



### QUICK REFERENCE DATA

$$V_R = 40 \text{ V}/45 \text{ V}$$

$$I_{O(AV)} = 2 \text{ A}$$

$$V_F \le 0.45 \text{V}$$

### **GENERAL DESCRIPTION**

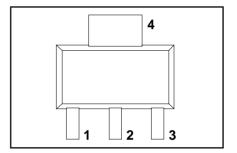
Dual, common cathode schottky rectifier diodes in a plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR245CT series is supplied in the surface mounting SOT223 package.

### **PINNING**

PIN	DESCRIPTION	
1	anode 1	
2	cathode	
3	anode 2	
tab	cathode	

#### **SOT223**



## **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS MIN. MAX		XX.	UNIT	
		PBYR2		40CT	45CT	
$V_{RRM}$	Peak repetitive reverse voltage		-	40	45	V
$V_{RWM}$	Working peak reverse voltage		-	40	45	V
$V_R$	Continuous reverse voltage	T <sub>sp</sub> ≤ 74 °C	-	40	45	V
I <sub>O(AV)</sub>	Average rectified output current (both diodes conducting)	square wave; $\delta = 0.5$ ; $T_{sp} \le 119 ^{\circ}C$	-	2	2	A
I <sub>FRM</sub>	Repetitive peak forward current per diode	square wave; $\delta = 0.5$ ; $T_{sp} \le 119 ^{\circ}\text{C}$	-	2	2	A
I <sub>FSM</sub>	Non-repetitive peak forward current per diode	t = 10  ms t = 8.3  ms sinusoidal; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM(max)}}$	-	6.	6 .6	A A
I <sub>RRM</sub>	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T <sub>i max</sub>	-	1	1	A
T <sub>j</sub>	Operating junction temperature	Jillax	-	15	50	°C
T <sub>stg</sub>	Storage temperature		- 40	15	50	°C

### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
		pcb mounted, minimum footprint pcb mounted, pad area as in fig:1	-	156 70	-	K/W K/W

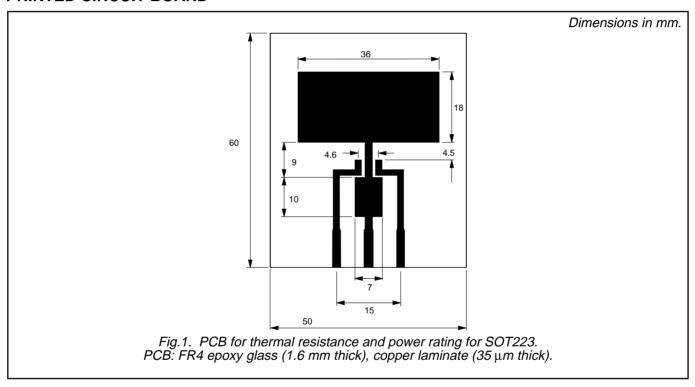
PBYR245CT series

## **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{F}$	Forward voltage	$I_F = 1 \text{ A}; T_i = 125^{\circ}\text{C}$	-	0.41	0.45	V
		$I_F = 2 \text{ A}$	-	0.58	0.7	V
$I_R$	Reverse current	$V_R = V_{RWM}$	-	0.03	0.2	mΑ
		$V_{R} = V_{RWM}$ ; $T_{j} = 100^{\circ}C$	-	1.5	10	mΑ
C <sub>d</sub>	Junction capacitance	$V_R = 5 \text{ W}$ ; $f = 1 \text{ MHz}$ , $T_i = 25 \text{ C}$ to $125 \text{ C}$	-	60	-	pF

## PRINTED CIRCUIT BOARD



### PBYR245CT series

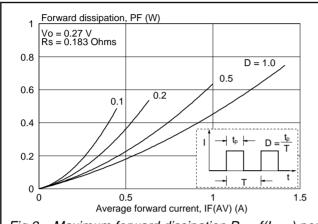


Fig.2. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; square current waveform where  $I_{F(AV)} = I_{F(RMS)} x \sqrt{D}$ .

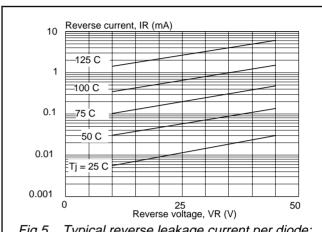


Fig.5. Typical reverse leakage current per diode;  $I_R = f(V_R)$ ; parameter  $T_j$ 

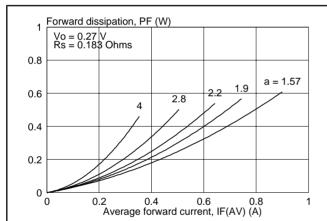


Fig.3. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; sinusoidal current waveform where a = f form factor  $= I_{F(RMS)} / I_{F(AV)}$ .

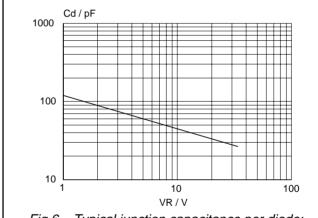


Fig.6. Typical junction capacitance per diode;  $C_d = f(V_R)$ ; f = 1 MHz;  $T_j = 25$ °C to 125°C.

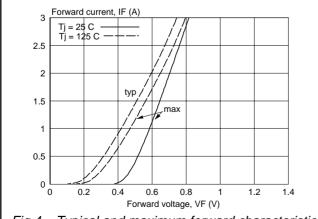


Fig.4. Typical and maximum forward characteristic  $I_F = f(V_F)$ ; parameter  $T_i$ 

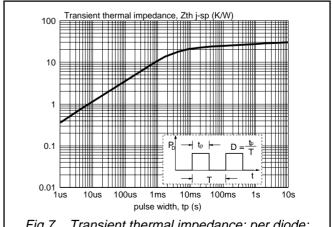
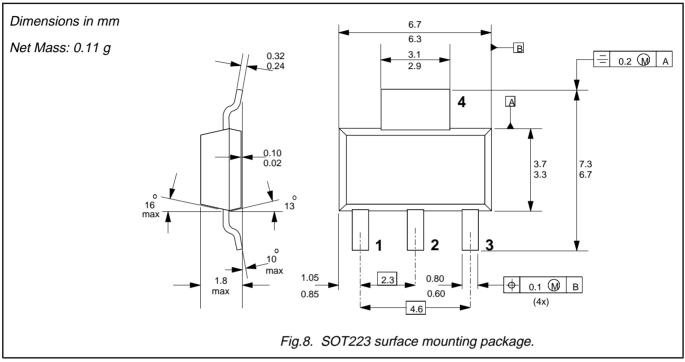


Fig.7. Transient thermal impedance; per diode;  $Z_{th j\text{-sp}} = f(t_p)$ .

## PBYR245CT series

## **MECHANICAL DATA**



## **Notes**

- For further information, refer to Philips publication SC18 " SMD Footprint Design and Soldering Guidelines".
   Order code: 9397 750 00505.
   Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors **Product specification** 

Rectifier diodes	PBYR245CT series
Schottky barrier	

#### **DEFINITIONS**

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limiting values				

#### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### Application information

Where application information is given, it is advisory and does not form part of the specification.

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